



# CPH3360

## P-Channel Power MOSFET -30V, -1.6A, 303mΩ, Single CPH3

ON Semiconductor®

<http://onsemi.com>

### Features

- ON-resistance  $R_{DS(on)1}=233m\Omega$ (typ.)
- 4V drive
- Halogen free compliance

### Specifications

#### Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	$V_{DSS}$		-30	V
Gate to Source Voltage	$V_{GSS}$		$\pm 20$	V
Drain Current (DC)	$I_D$		-1.6	A
Drain Current (Pulse)	$I_{DP}$	$PW \leq 10\mu\text{s}$ , duty cycle $\leq 1\%$	-6.4	A
Allowable Power Dissipation	$P_D$	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)	0.9	W
Channel Temperature	$T_{ch}$		150	°C
Storage Temperature	$T_{stg}$		-55 to +150	°C

This product is designed to "ESD immunity < 200V\*\*", so please take care when handling.

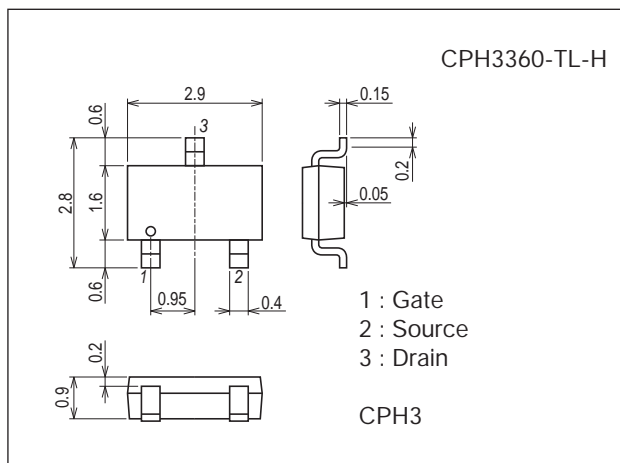
\* Machine Model

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### Package Dimensions

unit : mm (typ)

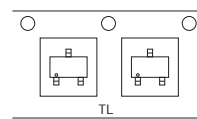
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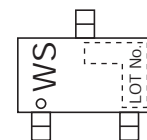
### Product & Package Information

- Package : CPH3
- JEITA, JEDEC : SC-59, TO-236, SOT-23
- Minimum Packing Quantity : 3,000 pcs./reel

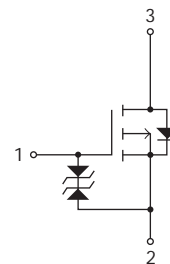
### Packing Type: TL



### Marking



### Electrical Connection

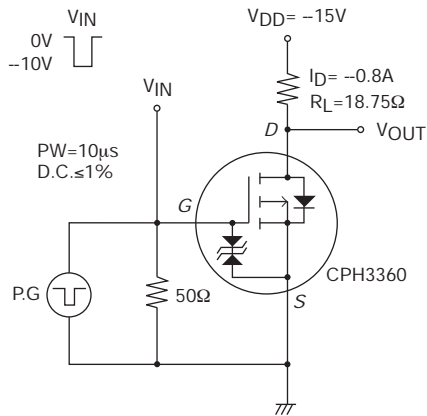


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## Electrical Characteristics at Ta=25°C

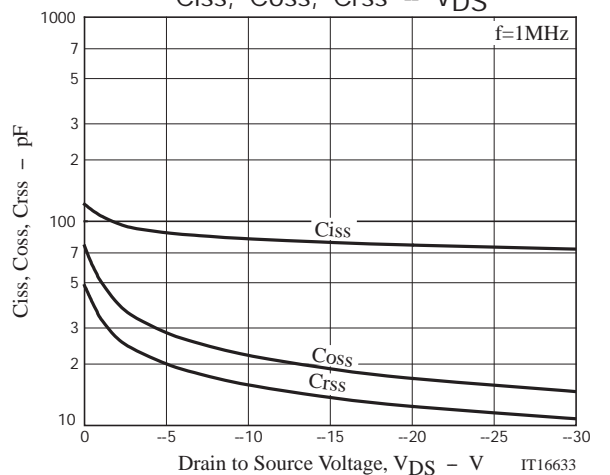
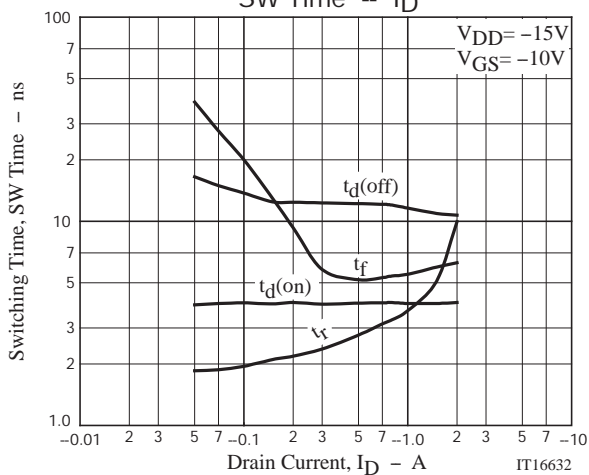
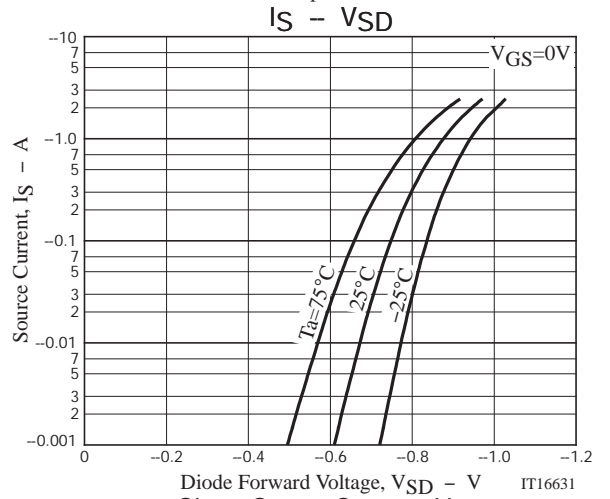
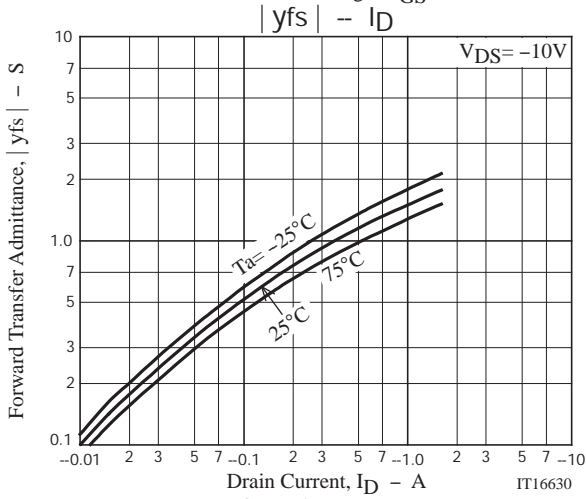
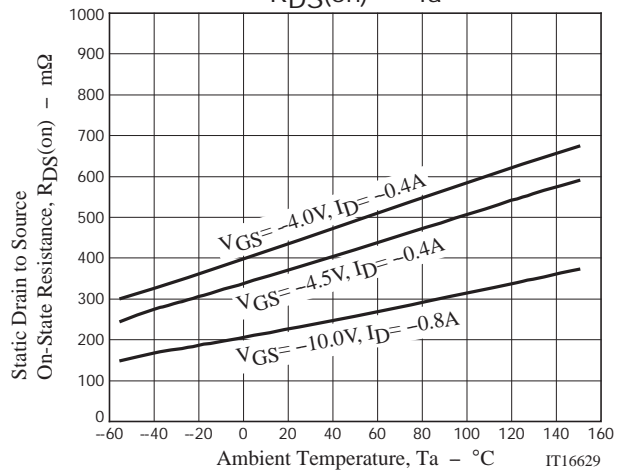
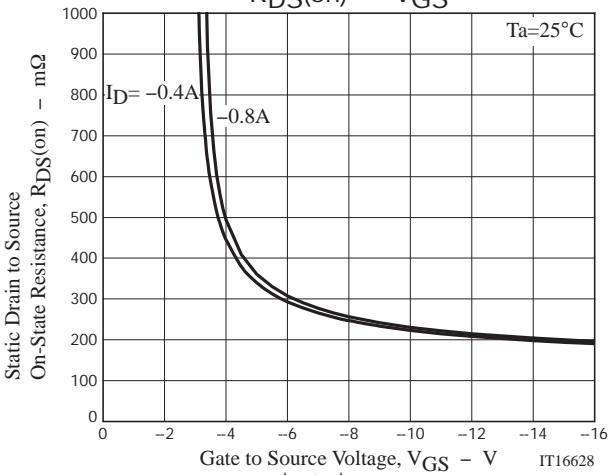
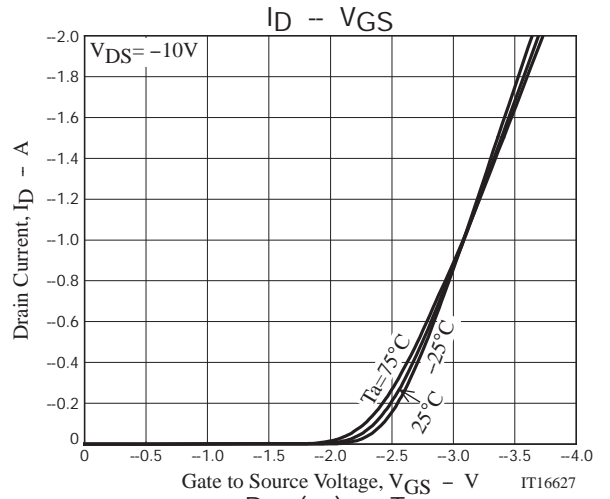
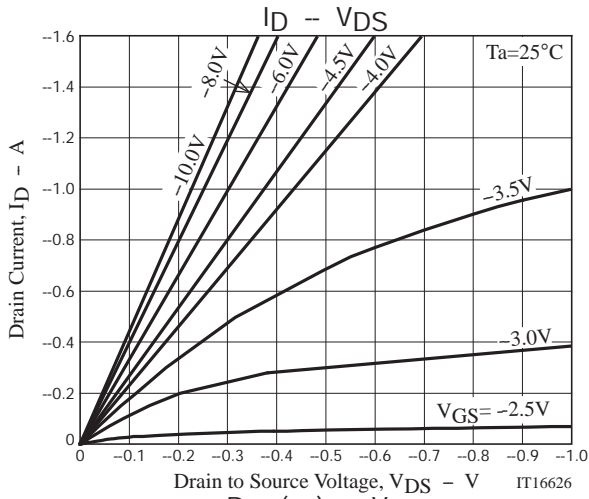
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0V	-30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μA
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-0.8A		1.3		S
Static Drain to Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-0.8A, V <sub>GS</sub> =-10V		233	303	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-0.4A, V <sub>GS</sub> =-4.5V		380	532	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =-0.4A, V <sub>GS</sub> =-4V		441	617	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-10V, f=1MHz		82		pF
Output Capacitance	C <sub>oss</sub>			22		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			16		pF
Turn-ON Delay Time	t <sub>d(on)</sub>		See specified Test Circuit.		4.0	
Rise Time	t <sub>r</sub>			3.3		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>			12		ns
Fall Time	t <sub>f</sub>			5.4		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-1.6A			2.2	
Gate to Source Charge	Q <sub>gs</sub>			0.36		nC
Gate to Drain "Miller" Charge	Q <sub>gd</sub>			0.49		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1.6A, V <sub>GS</sub> =0V		-0.9	-1.5	V

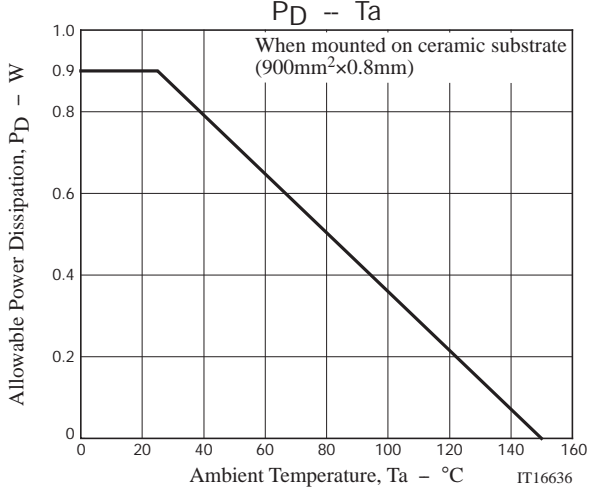
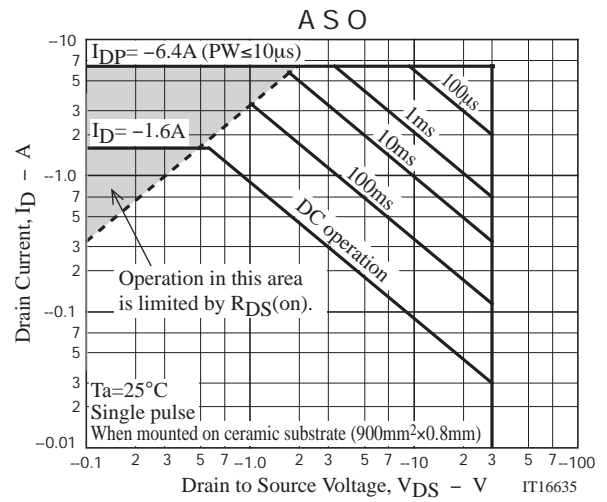
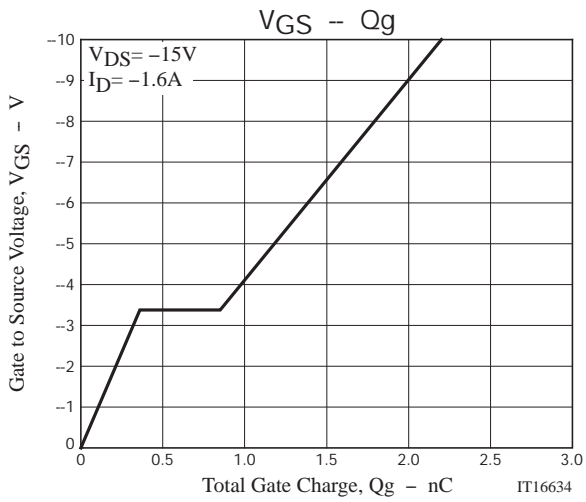
## Switching Time Test Circuit



## Ordering Information

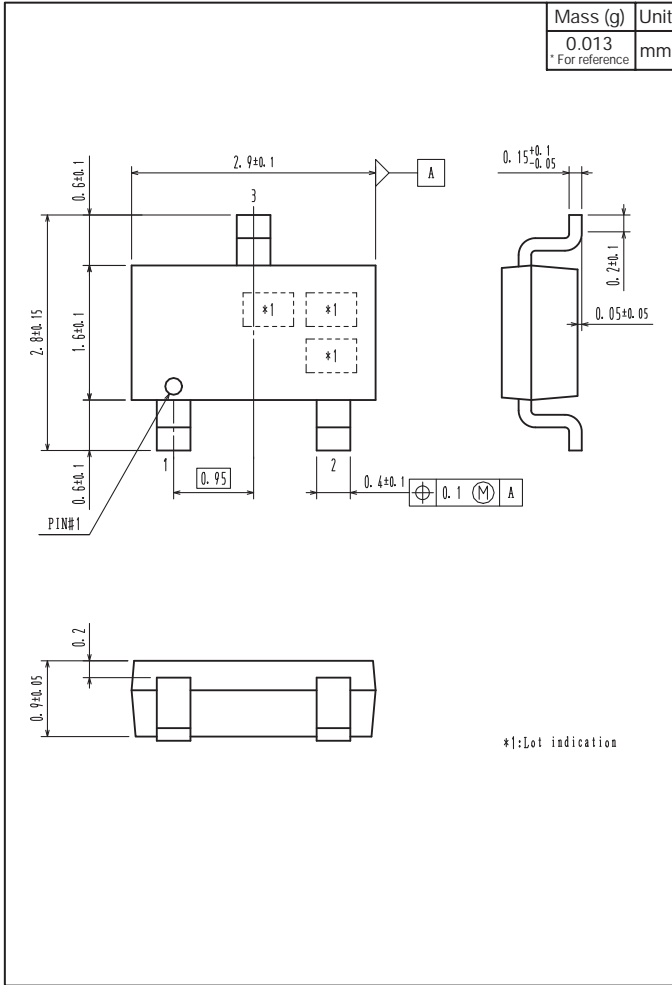
Device	Package	Shipping	memo
CPH3360-TL-H	CPH3	3,000pcs./reel	Pb-Free and Halogen Free



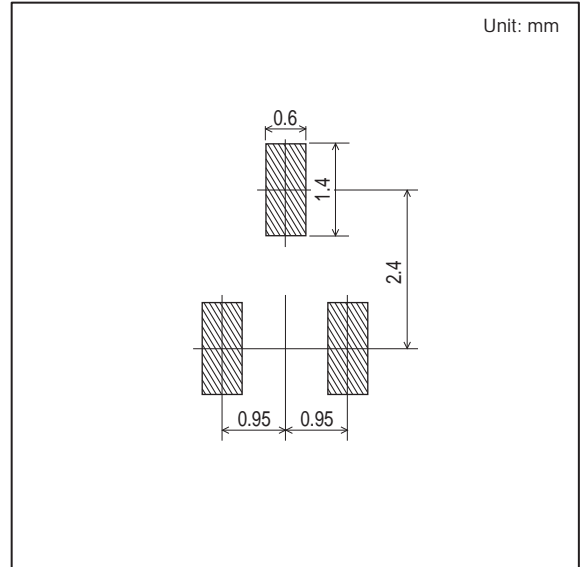


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## Outline Drawing CPH3360-TL-H



## Land Pattern Example



Note on usage : Since the CPH3360 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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